



# **General Description**

The WSF12N15 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF12N15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

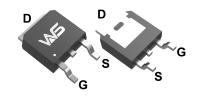
# **Product Summery**

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
150V	230mΩ	10A

# **Applications**

- High-Frequency Switch
- Load Switch
- Motion Switch

# **TO-252 Pin Configuration**





# **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	150	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	10	Α	
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	6	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	25	Α	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	6.25	mJ	
I <sub>AS</sub>	Avalanche Current	5	Α	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>3</sup>	27	W	
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	2.0	W	
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C	

# **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>		62.5	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		4.6	°C/W



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	150			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.098		V/°C
D	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =2A		225	290	mΩ
R <sub>DS(ON)</sub>		V <sub>GS</sub> =4.5V , I <sub>D</sub> =1.5A		260	350	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V V 1 252 A	1.2	1.8	2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250uA$		-4.57		mV/°C
	Duit Constitution Const	V <sub>DS</sub> =120V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =120V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	- uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
Qg	Total Gate Charge (10V)	V <sub>DS</sub> =75V , V <sub>GS</sub> =10V , I <sub>D</sub> =2A		15		
$Q_{gs}$	Gate-Source Charge			3.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			3.2		
T <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD}$ =75V , $V_{GS}$ =10V , $R_G$ =6 $\Omega$ $I_D$ =1A.		11		
Tr	Rise Time			8		]
T <sub>d(off)</sub>	Turn-Off Delay Time			29		ns
T <sub>f</sub>	Fall Time			10		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , f=1MHz		755		
C <sub>oss</sub>	Output Capacitance			65		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			18		

# **Diode Characteristics**

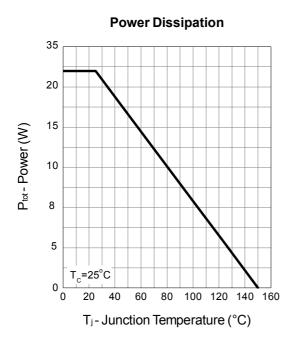
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			10	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.3	V
t <sub>rr</sub>	Reverse Recovery Time			38		nS
Q <sub>rr</sub>	Reverse Recovery Charge	IF=2A , dI/dt=100A/μs , T <sub>J</sub> =25°C		65		nC

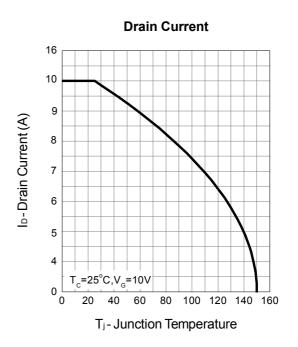
### Note:

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leqq$  300us , duty cycle  $\leqq$  2%
- 3 .The EAS data shows Max. rating . The test condition is  $V_{DD}$ =72V, $V_{GS}$ =10V,L=0.5mH, $I_{AS}$ =5A
- 4.The power dissipation is limited by 150°C junction temperature
- 5 .The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

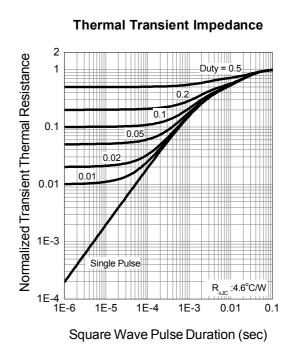


# **Typical Operating Characteristics**



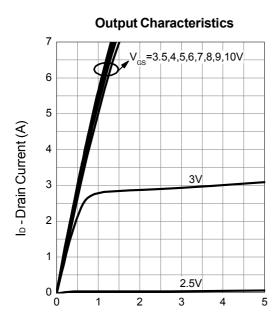


# Safe Operation Area $(V) = \frac{100}{100 \text{ Joseph Policy of Policy$

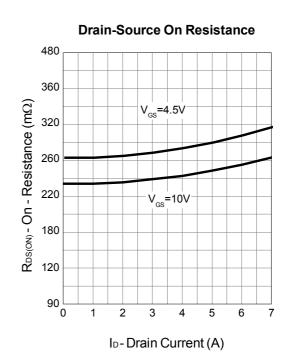




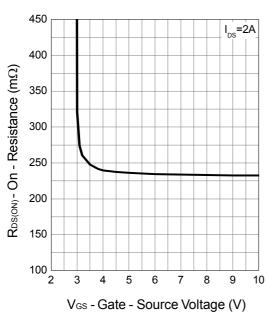
# **Typical Operating Characteristics**



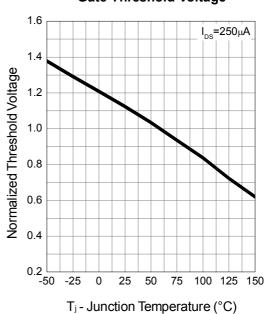
V<sub>DS</sub> - Drain - Source Voltage (V)



# **Gate-Source On Resistance**

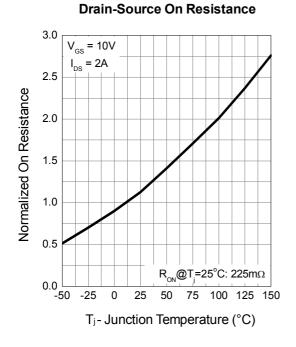


# **Gate Threshold Voltage**

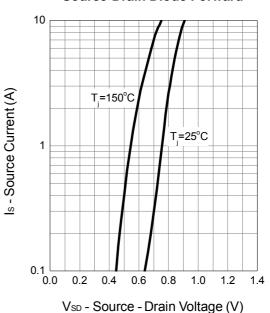




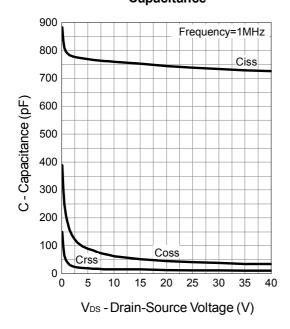
# **Typical Operating Characteristics (Cont.)**



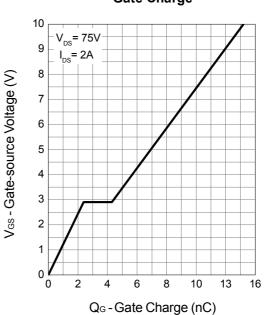
### Source-Drain Diode Forward



# Capacitance



# **Gate Charge**





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